

BDW94/A/B/C

Power Linear and Switching Applications

- Power Darlington TR
- Complement to BDW93, BDW93A, BDW93B and BDW93C respectively



1.Base 2.Collector 3.Emitter

PNP Epitaxial Silicon Transistor

Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage		
	: BDW94	- 45	V
	: BDW94A	- 60	V
	: BDW94B	- 80	V
	: BDW94C	- 100	V
V _{CEO}	Collector-Emitter Voltage		
	: BDW94	- 45	V
	: BDW94A	- 60	V
	: BDW94B	- 80	V
	: BDW94C	- 100	V
I _C	Collector Current (DC)	- 12	Α
I _{CP}	*Collector Current (Pulse)	- 15	Α
I _B	Base Current	- 0.2	Α
P _C	Collector Dissipation (T _C =25°C)	80	W
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	- 65 ~ 150	°C

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Electrical	Characteristics	T _C =25°C unless otherwise noted
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Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{CEO} (sus)	Collector-Emitter Sustaining Voltage	100 4 1 0	45			.,
	: BDW94	$I_C = -100 \text{mA}, I_B = 0$	- 45			V
	: BDW94A		- 60			V
	: BDW94B		- 80			V
-	: BDW94C		- 100			V
I_{CBO}	Collector Cut-off Current					
	: BDW94	$V_{CB} = -45V, I_{E} = 0$			- 100	μΑ
	: BDW94A	$V_{CB} = -60V, I_{E} = 0$			- 100	μΑ
	: BDW94B	$V_{CB} = -80V, I_{E} = 0$			- 100	μΑ
	: BDW94C	$V_{CB} = -100V, I_{E} = 0$			- 100	μΑ
I _{CEO}	Collector Cut-off Current					
	: BDW94	$V_{CE} = -45V, I_{B} = 0$			-1	mA
	: BDW94A	$V_{CE} = -60V, I_{B} = 0$			- 1	mA
	: BDW94B	$V_{CE} = -80V, I_{B} = 0$			- 1	mA
	: BDW94C	$V_{CE} = -100V, I_{B} = 0$			- 1	mA
I _{EBO}	Emitter Cut-off Current	$V_{EB} = -5V, I_{C} = 0$			- 2	mA
h _{FE}	* DC Current Gain	$V_{CE} = -3V, I_{C} = -3A$	1000			
		$V_{CE} = -3V, I_{C} = -5A$	750		20000	
		$V_{CE} = -3V, I_{C} = -10A$	100			
V _{CE} (sat)	* Collector-Emitter Saturation Voltage	$I_C = -5A$, $I_B = -20mA$			- 2	V
		$I_C = -10A$, $I_B = -100mA$			- 3	V
V _{BE} (sat)	* Base-Emitter Saturation Voltage	I _C = - 5A, I _B = - 20mA			- 2.5	V
		$I_C = -10A$, $I_B = -100mA$			- 4	V
V _F	* Parallel Diode Forward Voltage	I _F = - 5A		- 1.3	- 2	V
		I _F = -1 0A		- 1.8	- 4	V

^{*} Pulse Test: PW=300μs, duty Cycle =1.5% Pulsed

Typical Characteristics

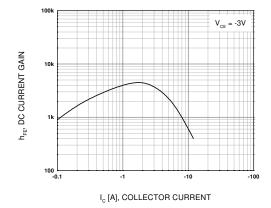


Figure 1. DC Current Gain

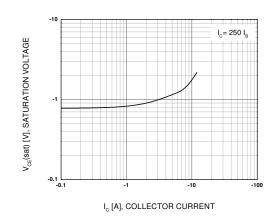


Figure 2. Collector-Emitter Saturation Voltage

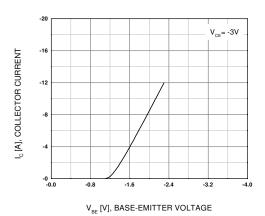


Figure 3. Base-Emitter On Voltage

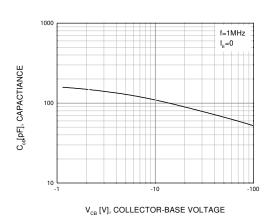


Figure 4. Output Capacitance

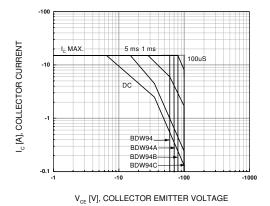


Figure 5. Safe Operating Area

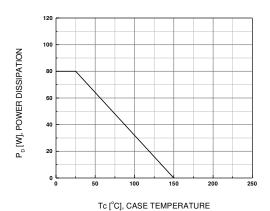
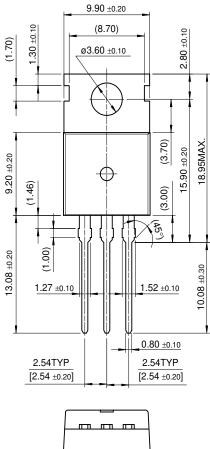


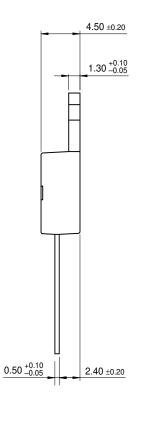
Figure 6. Power Derating

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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